

Efficient Power Conversion with MCC's SiC MOSFETs in 1200V & 1700V

SICW080N120Y4-BP SICW1000N170A-BP

SiC MOSFETs



Features

- Optimized for higher switching frequency
- High blocking voltage with low on-resistance
- Stable on-resistance over temperature
- Reduced heat sink requirements
- Avalanche capability
- Improved power conversion efficiency
- Cost-effective and compact design



Benefits

These SiC MOSFETs can withstand high voltage spikes without damage, enhancing durability and reliability in demanding applications.

MCC's SiC solutions are designed to operate at a high switching frequency, allowing for faster switching and higher efficiency in power conversion applications.

Applications



Industrial Motor Drives



Solar Inverters

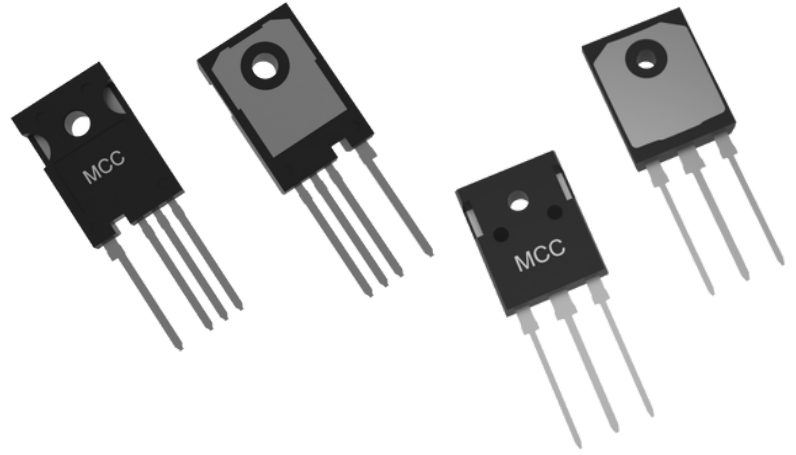


Telecom



IMPROVE PERFORMANCE AND REDUCE SYSTEM SIZE

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Parametrics & Datasheets:

Product	Drain-Source Voltage VDS	Gate-Source Voltage VGSmax	Continuous Drain Current ID	RDS(ON) Max	VGS(th) Max	Package Type	Data Sheet
SICW080N120Y4-BP	1200V	-8/+22	38A	85mΩ	3.6V	TO-247-4	Info
SICW1000N170A-BP	1700V	-5/+25	3A	1370mΩ	4.5V	TO-247AB	Info

Applications:



Industrial



Renewables



Communications

- Industrial motor drives
- Power supplies/uninterruptible power supplies (UPS)
- Switched-mode power supplies (SMPS)
- High-frequency power amplifiers
- RF applications
- Industrial heating and drying systems
- Scientific research and testing equipment
- Off-board chargers

- Solar inverters
- Energy storage systems (ESS)
- Wind turbine converters

- RF power amplifiers in satellite communication and radar systems
- Server/telecom for high-speed (fiber-optic) transceivers

CONTACT MCC TO REQUEST A SAMPLE

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